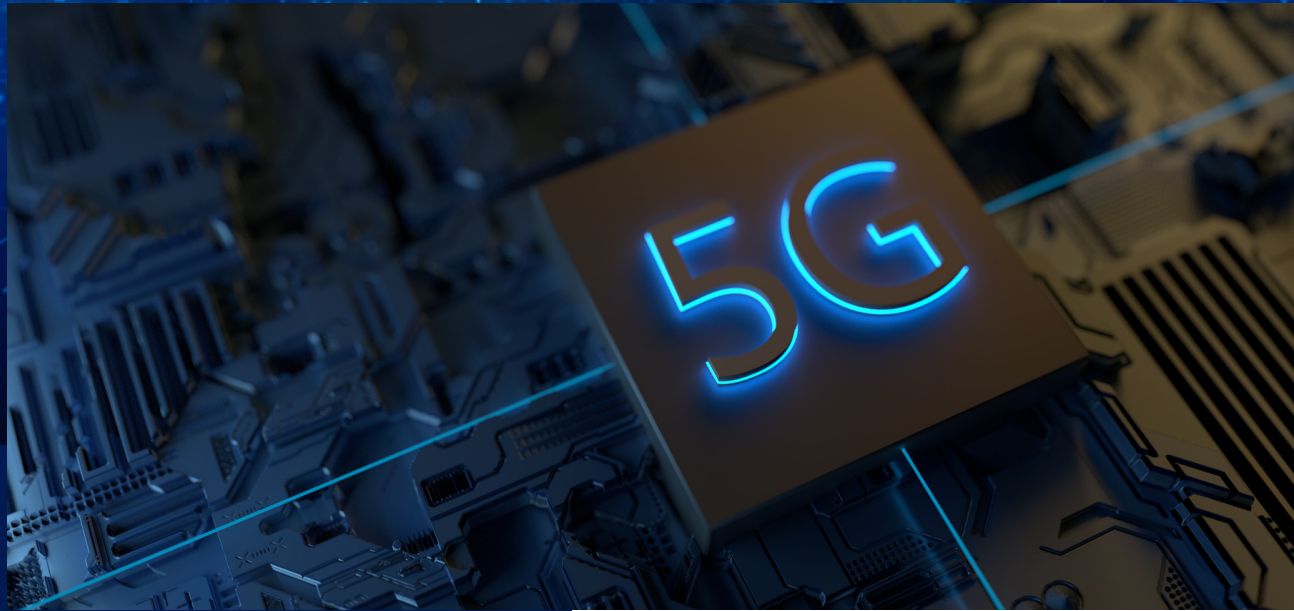


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WHY THIS ARTICLE MATTERS



EE|Times

Finwave to Push GaN Technology
Boundaries

With a new CEO on board, startup Finwave Semiconductor was eager to get his name out there and continue to build recognition for the company, which had just exited stealth mode the year prior. Enter one of the most respected semiconductor journalists, Dr. Maurizio Di Paolo Emilio, writing for EE Times. Through regular touchpoints where we provided a range of insight, we secured a number of earned media opportunities for Finwave, including this in-depth interview with the new CEO, which details the company's unique technology and his vision for Finwave's future.

FINWAVE

Finwave Semiconductor is shaping the future through a new generation of RF and power chips based on a breakthrough Gallium Nitride (GaN) transistor architecture. Finwave's advanced 3DGaN™ technology is the discovery of prominent MIT innovators who are focused on bringing the true potential of GaN to key industries including 5G, AI, cloud computing, and EV and autonomous vehicles.